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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: Not yet assigned  
Applicants: Eri TSUKADA, et al.  
Filed Internationally: January 19, 2005  
US National: Herewith  
Title: METHOD FOR PRODUCING SILICON NITRIDE FILMS AND  
SILICON OXYNITRIDE FILMS BY CHEMICAL VAPOR  
DEPOSITION  
TC/A.U.: Unknown  
Examiner: Unknown  
Docket No.: Serie 6497  
Customer No.: 000040582

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Prior to an examination of the merits of the above-identified U.S. patent application under 37 C.F.R. § 1.115, please first amend the application as follows:

**Amendments to the Claims** begin on page 2 of this paper.

**Remarks** begin on page 4 of this paper.

An **Appendix** including the Abstract is attached following page 4 of this paper.